

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

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20V Dual N-Channel MOSFET w/ESD Protected

TSSOP-8

Pin Definition:

8 1. Dr 2. Sc 3. Sc 4. Ge

- 1. Drain 1 8. Drain 2 2. Source 1 7. Source 2 3. Source 1 6. Source 2
- 4. Gate 1 5. Gate 2

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
20	22 @ V _{GS} = 4.5V	6.5
	29 @ V _{GS} = 2.5V	5.5

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance
- ESD Protect 2KV

Application

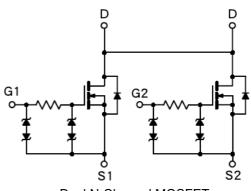
- Specially Designed for Li-on Battery Packs
- Battery Switch Application

Ordering Information

Part No.	Package	Packing
TSM6968DCA RVG	TSSOP-8	3Kpcs / 13" Reel

Note: "G" denotes for Halogen Free

Block Diagram



Dual N-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V _{DS}	20	V
Gate-Source Voltage		V_{GS}	±12	V
Continuous Drain Current, V _{GS} @4.5	V.	I _D	6.5	Α
Pulsed Drain Current, V _{GS} @4.5V		I _{DM}	30	A
Continuous Source Current (Diode C	conduction) ^{a,b}	Is	1.4	А
Maximum Power Dissipation	Ta = 25°C	В	1.04	14/
	Ta = 75°C	P _D	0.625	W
Operating Junction Temperature		TJ	+150	°C
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Foot (Drain) Thermal Resistance	$R\Theta_{JF}$	83	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	$R\Theta_{JA}$	120	°C/W

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, t ≤ 5 sec.





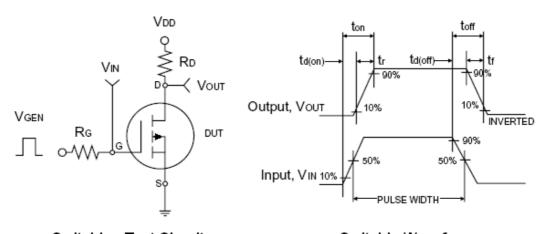
20V Dual N-Channel MOSFET w/ESD Protected

Electrical Specifications (Ta = 25°C, unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static		1		1		•
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	0.6	0.8	1.0	V
Gate Body Leakage	$V_{GS} = \pm 12V, V_{DS} = 0V$	I _{GSS}			±10	uA
Zero Gate Voltage Drain Current	$V_{DS} = 16V, V_{GS} = 0V$	I _{DSS}			1.0	uA
On-State Drain Current	$V_{DS} = 5V, V_{GS} = 4.5V$	I _{D(ON)}	30			Α
Drain Course On State Besistance	$V_{GS} = 4.5V, I_D = 6.0A$			15	22	0
Drain-Source On-State Resistance	rain-Source On-State Resistance $V_{GS} = 2.5V$, $I_D = 5.0A$ $R_{DS(ON)}$		20	29	mΩ	
Forward Transconductance	$V_{DS} = 10V, I_D = 6.5A$	g _{fs}		16		S
Diode Forward Voltage	$I_S = 1.7A, V_{GS} = 0V$	V_{SD}		0.6	1.2	V
Dynamic ^b						
Total Gate Charge	10\/ 1 6 A	Q_g		15	20	
Gate-Source Charge	$V_{DS} = 10V, I_D = 6A,$ $V_{GS} = 4.5V$	Q_gs		3.4		nC
Gate-Drain Charge	V _{GS} = 4.5 V	Q_gd		1.2		
Input Capacitance	\/ 40\/ \/ 0\/	C_{iss}		950		
Output Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$	C_{oss}		450		pF
Reverse Transfer Capacitance	f = 1.0MHz	C_{rss}		135		
Switching ^c						
Turn-On Delay Time	V 40V D 400	t _{d(on)}		140	200	
Turn-On Rise Time	$V_{DD} = 10V, R_{L} = 10\Omega,$	t _r		210	250	0
Turn-Off Delay Time	$I_D = 1A$, $V_{GEN} = 4.5V$,	t _{d(off)}		3700	4800	nS
Turn-Off Fall Time	$R_{G} = 6\Omega$	t _f		2000	2600	

Notes:

- a. pulse test: PW $\leq 300 \mu S$, duty cycle $\leq 2\%$ b. For DESIGN AID ONLY, not subject to production testing. b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

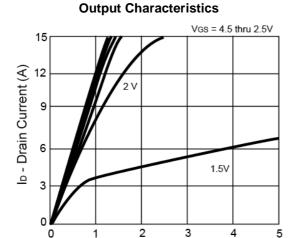
Switchin Waveforms



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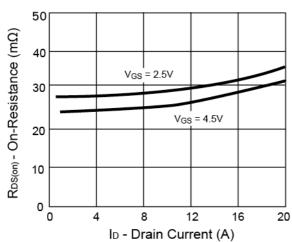


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

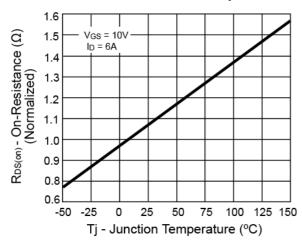


On-Resistance vs. Drain Current

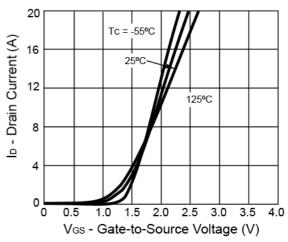
VDS - Drain-to-Source Voltage (V)



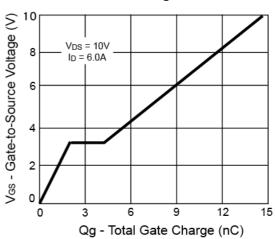
On-Resistance vs. Junction Temperature



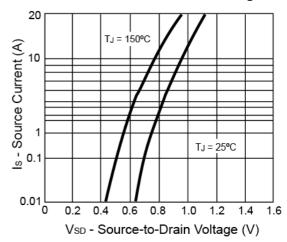
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



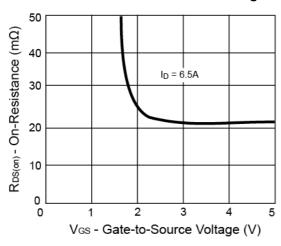


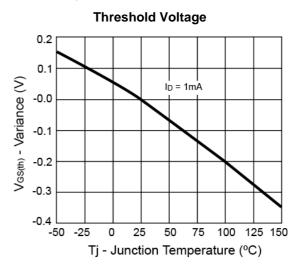


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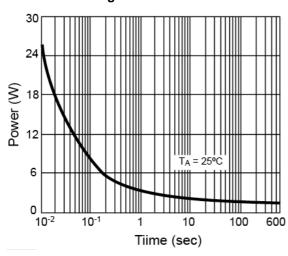
Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

On-Resistance vs. Gate-Source Voltage

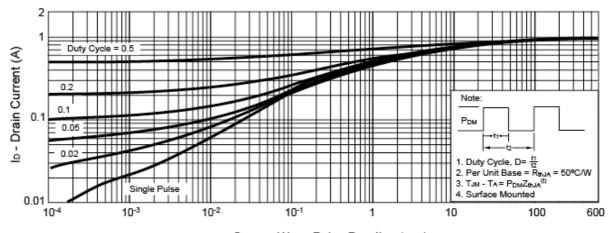




Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



Square Wave Pulse Duration (sec)

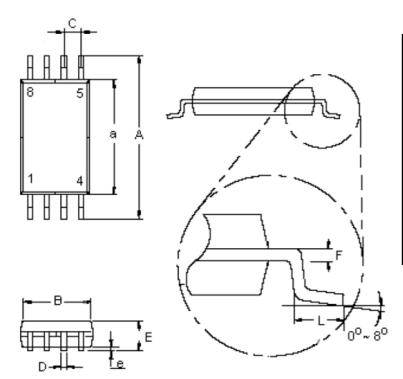
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TSSOP-8 Mechanical Drawing



TSSOP-8 DIMENSION				
DIM	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	6.20	6.60	0.244	0.260
а	4.30	4.50	0.170	0.177
В	2.90	3.10	0.114	0.122
С	0.65 (typ)		0.025 (typ)	
D	0.25	0.30	0.010	0.019
Е	1 OF	4.00	0.044	0.040
. –	1.05	1.20	0.041	0.049
e	0.05	0.15	0.041	0.049
			0.002	
e	0.05		0.002	0.009

Marking Diagram



Y = Year Code

M = Month Code for Halogen Free Product

O =Jan P =Feb Q =Mar R =Apr

S = May T = Jun U = Jul V = Aug

W = Sep X = Oct Y = Nov Z = Dec

L = Lot Code



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